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(54) Title: METHOD OF BONDING USING A BONDING LAYER BASED ON ZINC, SILICON AND OXYGEN AND CORRESPONDING STRUCTURES

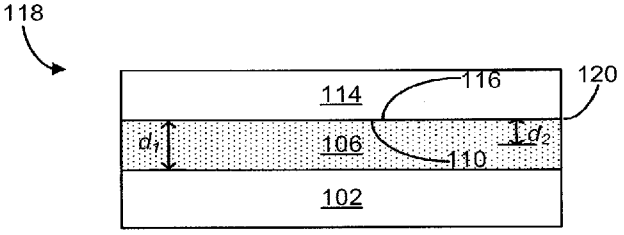



Fig. 1D

(57) Abstract: Embodiments of the invention relate to methods and structures for fabricating semiconductor structures that include at least one bonding layer (106) for attaching two or more elements (102, 114) to one another. The at least one bonding layer may be at least substantially comprised of zinc, silicon and oxygen.

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